

CLAIM AMENDMENTS

Please cancel Claims 1, 2, 4-24, and 26-38, and amend Claim 3 and 25 as follows:

1.-2. (Cancelled)

3. (Currently Amended) ~~The~~ A semiconductor member according to claim 1, further comprising:

a first porous semiconductor layer which is made of a strain inducing material on a semiconductor substrate;

a strained semiconductor layer which is formed on the first porous semiconductor layer; and

a second porous semiconductor layer made of the same material as the semiconductor substrate between the semiconductor substrate and said first porous semiconductor layer made of the strain ~~induction~~ inducing material.

4.-24. (Cancelled)

25. (Currently Amended) ~~The~~ A semiconductor member according to claim 20, further comprising:

a first porous semiconductor layer which is made of a strain inducing material on a semiconductor substrate;

a second porous semiconductor layer which is formed on the first porous semiconductor layer;

a strained semiconductor layer which is formed on the second porous semiconductor layer; and

a third porous semiconductor layer made of the same material as the semiconductor substrate between the semiconductor substrate and said first porous semiconductor layer made of the strain ~~induction~~inducing material.

26.-38. (Cancelled)